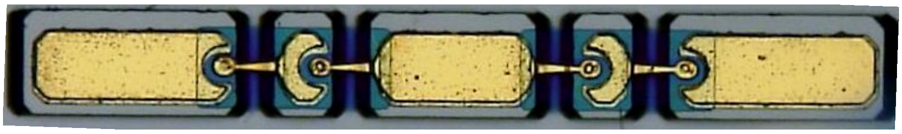
Anti-series Air-bridged Schottky Diodes

GaAs varactor diodes



Features

- Gold air-bridged structure
- Very low parasitic capacitance
- Very low junction capacitance
- Low series resistance
- 100% electrically tested
- 100% visual inspection

Part number	Anode area (µm^2)	Junction capacitance (fF)
AS3/4G2/18P6	18.6	27.74
AS3/4G2/21P6	21.6	32.18
AS3/4G2/24P8	24.8	36.95
AS3/4G2/28P1	28.1	41.87
AS3/4G2/31P6	31.6	47.08
AS3/4G2/35P0	35.0	52.15
AS3/4G2/38P3	38.3	57.07

Chip parameters

Parameter	Unit	Min.	Typ.	Max.
Chip length	µm	326	336	346
Chip width	µm	46	56	66
Chip thickness	µm	45	50	55

Part Number Guide

XXN / NYN / NNPN

Diode configuration		Chip details			Anode
Diode series	Series number	Number of anodes	Substrate material	Schottky doping density x10^{17}cm^{-3}	Anode area µm^2

To order these diodes please contact sales@teratechcomponents.com
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